Preferred Device

Amplifier Transistors

PNP Silicon

Features

• Pb-Free Packages are Available*

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector – Emitter Voltage	V _{CEO}	120	Vdc
Collector - Base Voltage	V _{CBO}	130	Vdc
Emitter – Base Voltage	V _{EBO}	5.0	Vdc
Collector Current – Continuous	I _C	600	mAdc
Total Device Dissipation @ T _A = 25°C Derate above 25°C	P _D	625 5.0	mW mW/°C
Total Device Dissipation @ T _C = 25°C Derate above 25°C	P _D	1.5 12	W mW/°C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-55 to +150	°C

THERMAL CHARACTERISTICS

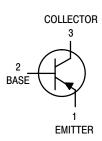
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	200	°C/W
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	83.3	°C/W

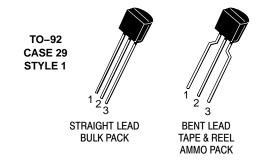
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.



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MARKING DIAGRAM



A = Assembly Location

Y = Year

WW = Work Week

= Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

Preferred devices are recommended choices for future use and best overall value.

^{*}For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS	•		•	•
Collector-Emitter Breakdown Voltage (Note 1) (I _C = 1.0 mAdc, I _B = 0)	V _{(BR)CEO}	120	_	Vdc
Collector–Base Breakdown Voltage ($I_C = 100 \mu Adc, I_E = 0$)	V _{(BR)CBO}	130	_	Vdc
Emitter–Base Breakdown Voltage ($I_E = 10 \mu Adc, I_C = 0$)	V _{(BR)EBO}	5.0	_	Vdc
Collector Cutoff Current	I _{CBO}	- -	100 100	nAdc μAdc
Emitter Cutoff Current (V _{EB} = 3.0 Vdc, I _C = 0)	I _{EBO}	-	50	nAdc
ON CHARACTERISTICS (Note 1)	<u>.</u>			
DC Current Gain ($I_C = 1.0 \text{ mAdc}, V_{CE} = 5.0 \text{ Vdc}$)	h _{FE}	30	_	_
$(I_C = 10 \text{ mAdc}, V_{CE} = 5.0 \text{ Vdc})$		40	180	
$(I_C = 50 \text{ mAdc}, V_{CE} = 5.0 \text{ Vdc})$		40	_	
Collector–Emitter Saturation Voltage ($I_C = 10 \text{ mAdc}$, $I_B = 1.0 \text{ mAdc}$) ($I_C = 50 \text{ mAdc}$, $I_B = 5.0 \text{ mAdc}$)	V _{CE(sat)}	- -	0.2 0.5	Vdc
Base – Emitter Saturation Voltage ($I_C = 10 \text{ mAdc}$, $I_B = 1.0 \text{ mAdc}$) ($I_C = 50 \text{ mAdc}$, $I_B = 5.0 \text{ mAdc}$)	V _{BE(sat)}	- -	1.0 1.0	Vdc
SMALL-SIGNAL CHARACTERISTICS	<u>.</u>			
Current-Gain — Bandwidth Product ($I_C = 10 \text{ mAdc}$, $V_{CE} = 10 \text{ Vdc}$, $f = 100 \text{ MHz}$)	f _T	100	400	MHz
Output Capacitance ($V_{CB} = 10 \text{ Vdc}, I_E = 0, f = 1.0 \text{ MHz}$)	C _{obo}	_	6.0	pF
Small–Signal Current Gain ($I_C = 1.0 \text{ mAdc}, V_{CE} = 10 \text{ Vdc}, f = 1.0 \text{ kHz}$)	h _{fe}	30	200	-
Noise Figure (I _C = 250 μ Adc, V _{CE} = 5.0 Vdc, R _S = 1.0 k Ω , f = 1.0 kHz)	NF	_	8.0	dB

^{1.} Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2.0%.

ORDERING INFORMATION

Device	Package	Shipping [†]
2N5400	TO-92	5000 Unit / Bulk
2N5400G	TO-92 (Pb-Free)	5000 Unit / Bulk
2N5400RLRP	TO-92	2000 Tape & Reel
2N5400RLRPG	TO-92 (Pb-Free)	2000 Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

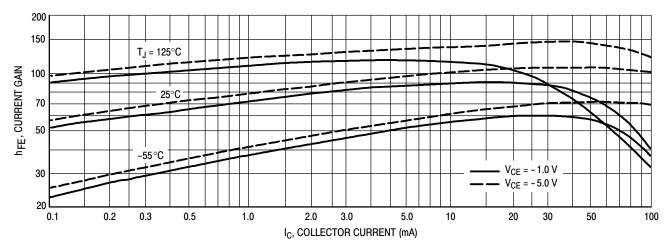


Figure 1. DC Current Gain

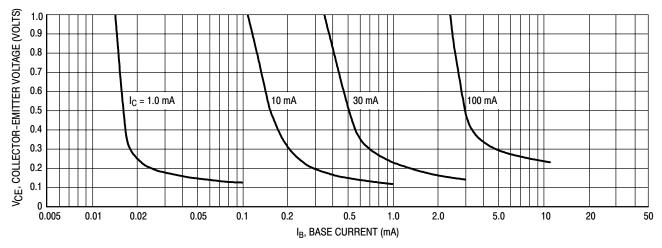


Figure 2. Collector Saturation Region

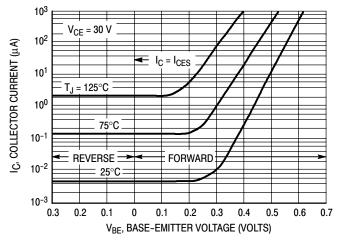


Figure 3. Collector Cut-Off Region

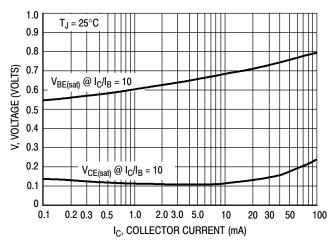


Figure 4. "On" Voltages

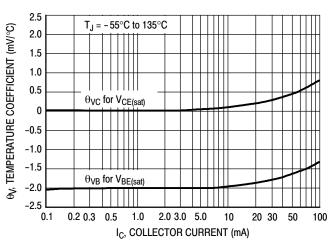
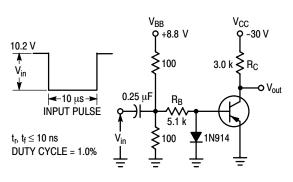


Figure 5. Temperature Coefficients



Values Shown are for I_C @ 10 mA

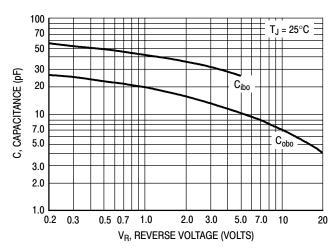


Figure 7. Capacitances

Figure 6. Switching Time Test Circuit

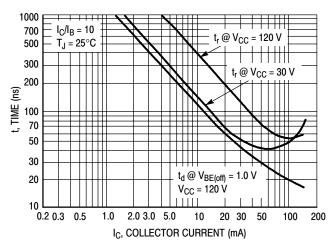


Figure 8. Turn-On Time

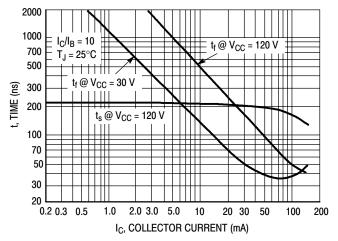
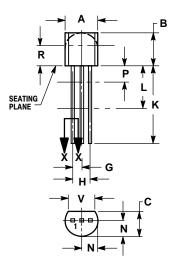


Figure 9. Turn-Off Time

PACKAGE DIMENSIONS

TO-92 (TO-226) CASE 29-11 **ISSUE AM**



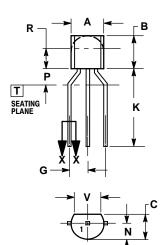
STRAIGHT LEAD **BULK PACK**



NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 CONTROLLING DIMENSION: INCH.
- CONTOUR OF PACKAGE BEYOND DIMENSION R
 IS UNCONTROLLED.
- LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	INCHES		MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.175	0.205	4.45	5.20
В	0.170	0.210	4.32	5.33
С	0.125	0.165	3.18	4.19
D	0.016	0.021	0.407	0.533
G	0.045	0.055	1.15	1.39
Н	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
K	0.500		12.70	
L	0.250		6.35	
N	0.080	0.105	2.04	2.66
Р		0.100	-	2.54
R	0.115		2.93	
V	0.135		3.43	



BENT LEAD TAPE & REEL AMMO PACK



NOTES:

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
 CONTROLLING DIMENSION:
- MILLIMETERS.
- DIMENSION R IS UNCONTROLLED.

 LEAD DIMENSION IS UNCONTROLLED IN
- P AND BEYOND DIMENSION K MINIMUM.

	MILLIMETERS		
DIM	MIN	MAX	
Α	4.45	5.20	
В	4.32	5.33	
С	3.18	4.19	
D	0.40	0.54	
G	2.40	2.80	
J	0.39	0.50	
K	12.70		
N	2.04	2.66	
P	1.50	4.00	
R	2.93		
٧	3.43		

PIN 1. EMITTER

BASE

COLLECTOR

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